Enrique Iborra

List of Publications by Year
in descending order

157	3,272	186265	161849
papers	citations	28 h-index	54 g-index

157	157	157	3577
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Direct growth of few-layer graphene on AlN-based resonators for high-sensitivity gravimetric biosensors. Beilstein Journal of Nanotechnology, 2019, 10, 975-984.	2.8	2
2	Impact of FBAR design on its sensitivity as in-liquid gravimetric sensor. Sensors and Actuators A: Physical, 2019, 289, 87-93.	4.1	12
3	Carbon nanotube isolation layer enhancing in-liquid quality-factors of thin film bulk acoustic wave resonators for gravimetric sensing. Sensors and Actuators B: Chemical, 2018, 261, 398-407.	7.8	10
4	AlN-Based Solidly Mounted Resonators on Glass Substrates for High Temperature Applications. , 2018, , .		2
5	Effects of Post-Deposition Vacuum Annealing on the Piezoelectric Properties of AlScN Thin Films Sputtered on 200 Mm Production Wafers. , 2018, , .		3
6	Resonant and Antiresonant Frequencies Behavior with Temperature Changes in Gravimetric Sensors. , 2018, , .		0
7	Reactive sputtering of AlScN thin Ulms with variable Sc content on 200 mm wafers. , 2018, , .		3
8	Selection of aptamers to Neisseria meningitidis and Streptococcus pneumoniae surface specific proteins and affinity assay using thin film AlN resonators. Sensors and Actuators B: Chemical, 2017, 246, 591-596.	7.8	4
9	Advances in piezoelectric thin films for acoustic biosensors, acoustofluidics and lab-on-chip applications. Progress in Materials Science, 2017, 89, 31-91.	32.8	467
10	Gravimetric sensors operating at 1.1â€‰GHz based on inclined c-axis ZnO grown on textured Al electrodes. Scientific Reports, 2017, 7, 1367.	3.3	15
11	Frequency response of AlN-based solidly mounted resonators under mechanical stress. Sensors and Actuators A: Physical, 2017, 258, 39-43.	4.1	2
12	The Influence of the Acoustic Reflector Design on the Temperature Coefficient of Frequency for Shear and Longitudinal Mode AlN Resonators. Journal of Microelectromechanical Systems, 2017, 26, 1306-1315.	2.5	2
13	Effects of compensating the temperature coefficient of frequency with the acoustic reflector layers on the overall performance of solidly mounted resonators. Ultrasonics, 2017, 74, 153-160.	3.9	7
14	Gravimetric biosensor based on a 1.3 GHz AlN shear-mode solidly mounted resonator. Sensors and Actuators B: Chemical, 2017, 239, 1282-1288.	7.8	43
15	AlN-solidly mounted resonators sustaining up to 1000Â°C with TCF compensation. , 2017, , .		9
16	Direct integration of CNT forests on solidly mounted resonators and their influence on device performance. , 2017, , .		3
17	Substrate texturing for homogeneous deposition of tilted c-axis AlN films for shear mode operation. , 2017, , .		0
18	Integration of multilayered graphene on AlN based resonators as a functionalization platform for biosensors. , 2017, , .		2

#	Article	IF	Citations
19	Integration and Bio-Functionalization of Vertically Aligned Carbon Nanotube Forests on High Frequency AlN Gravimetric Sensors. Proceedings (mdpi), 2017, 1, 537.	0.2	0
20	Integration of Graphene on AlN Based High Frequency Resonators and Their Functionalization for Biosensing. Proceedings (mdpi), 2017, 1, 539.	0.2	1
21	Scandium Aluminium Nitride-Based Film Bulk Acoustic Resonators. Proceedings (mdpi), 2017, 1, .	0.2	30
22	Bacteria Detection with High-frequency Gravimetric Biosensors Based on AlN Thin Film Resonators. Procedia Engineering, 2016, 168, 638-641.	1.2	1
23	Direct Comparison of the Sensitivity of QCMs and AlN-based TFRs Biosensors. Procedia Engineering, 2016, 168, 481-484.	1.2	0
24	High coupling phononic SH-SAW resonators for in-liquid operation. , 2016, , .		0
25	Transparent thin film bulk acoustic wave resonators. , 2016, , .		2
26	Influence of induced stress on AlN-solidly mounted resonators. , 2016, , .		0
27	S0 Lamb wave resonators for in-liquid sensing: Promising alternative to shear bulk acoustic wave devices. , 2016, , .		3
28	Tungsten Oxide Layers of High Acoustic Impedance for Fully Insulating Acoustic Reflectors. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2016, 63, 938-944.	3.0	5
29	Influence of liquid properties on the performance of S 0 â€mode Lamb wave sensors II: Experimental validation. Sensors and Actuators B: Chemical, 2016, 229, 331-337.	7.8	17
30	Effects of biologically compatible buffers on the electrical response of gravimetric sensors operating at GHz frequencies. Sensors and Actuators B: Chemical, 2016, 222, 688-692.	7.8	3
31	Room temperature sputtering of inclined c-axis ZnO for shear mode solidly mounted resonators. Applied Physics Letters, 2016, 108, 034103.	3.3	15
32	Carbon nanotube forests as top electrode in electroacoustic resonators. Applied Physics Letters, 2015, 107, .	3.3	7
33	Sputtered Al<inf>(1−x)</inf>Sc<inf>x</inf>N thin films with high areal uniformity for mass production. , 2015, , .		3
34	Assessment of the shear acoustic velocities in the different materials composing a high frequency solidly mounted resonator. Ultrasonics, 2015, 62, 195-199.	3.9	10
35	Carbon nanotube growth on piezoelectric AlN films: influence of catalyst underlayers. RSC Advances, 2015, 5, 80682-80687.	3.6	4
36	Optimized tilted c-axis AlN films for improved operation of shear mode resonators. Thin Solid Films, 2015, 590, 219-223.	1.8	26

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37	ZnO based SAW and FBAR devices for bio-sensing applications. Journal of Non-Newtonian Fluid Mechanics, 2015, 222, 209-216.	2.4	39
38	Discrete microfluidics based on aluminum nitride surface acoustic wave devices. Microfluidics and Nanofluidics, 2015, 18, 537-548.	2.2	46
39	Growth of carbon nanotube forests on metallic thin films. Carbon, 2015, 90, 9-15.	10.3	13
40	The influence of acoustic reflectors on the temperature coefficient of frequency of solidly mounted resonators. , 2014, , .		5
41	AlN shear mode solidly mounted resonator with temperature compensation for in-liquid sensing. , 2014, , .		1
42	ZnO/AlN stacked BAW resonators with double resonance. , 2014, , .		0
43	AlN solidly mounted resonators for high temperature applications. , 2014, , .		12
44	Carbon nanotube forests as top electrodes for AlN-based electroacoustic resonators. , 2014, , .		1
45	Microacoustic in-liquid sensors based on thin AlN films: A comparative study. , 2014, , .		0
46	Resistive switching in manganite/graphene hybrid planar nanostructures. Applied Physics Letters, 2014, 104, 102408.	3.3	6
47	Reversible electric-field control of magnetization at oxide interfaces. Nature Communications, 2014, 5, 4215.	12.8	59
48	On the effectiveness of lateral excitation of shear modes in AlN layered resonators. Ultrasonics, 2014, 54, 1504-1508.	3.9	17
49	Characterisation of aluminium nitride films and surface acoustic wave devices for microfluidic applications. Sensors and Actuators B: Chemical, 2014, 202, 984-992.	7.8	43
50	Influence of the electrical extensions in AlN-BAW resonators for in-liquid biosensors. , 2014, , .		9
51	Seed layer controlled deposition of ZnO films with a tilted c-axis for shear mode resonators. , 2014, , .		2
52	Assessment of the acoustic shear velocity in SiO2 and Mo layers for acoustic reflectors. , 2014, , .		1
53	Direct comparison of the gravimetric responsivities of ZnO-based FBARs and SMRs. Sensors and Actuators B: Chemical, 2013, 183, 136-143.	7.8	17
54	IR-reflectance assessment of the tilt angle of AlN-wurtzite films for shear mode resonators. , 2013, , .		1

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55	Induced surface roughness to promote the growth of tilted-AlN films for shear mode resonators. , 2013, , .		8
56	Piezoelectric and electroacoustic properties of V-doped and Ta-doped AlN thin films. , 2013, , .		12
57	Acoustic properties of carbon nanotube electrodes in BAW resonators. , 2013, , .		2
58	On the lateral excitation of shear modes in AlN layered resonators. , 2012, , .		2
59	Experimental comparison of FBARs and SMRs responsitivities to mass loadings. , 2012, , .		0
60	Piezoelectric and electroacoustic properties of Ti-doped AlN thin films as a function of Ti content. , 2012, , .		12
61	High-acoustic-impedance tantalum oxide layers for insulating acoustic reflectors. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2012, 59, 366-372.	3.0	18
62	Thermally assisted tunneling transport in La<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.7</mml:mn></mml:mrow></mml:msub></mml:math>Ca<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>0.3</mml:mn></mml:mrow></mml:msub></mml:math>MnO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow />	3.2	19
63	Influence of crystal quality on the excitation and propagation of surface and bulk acoustic waves in polycrystalline AlN films. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2012, 59, 128-134.	3.0	13
64	Low-thickness high-quality aluminum nitride films for super high frequency solidly mounted resonators. Thin Solid Films, 2012, 520, 3060-3063.	1.8	24
65	Characterization of amorphous tantalum oxide for insulating acoustic mirrors. , 2011, , .		4
66	Multiple frequency Solidly Mounted BAW filters. , 2011, , .		1
67	AlN-based BAW resonators with CNT electrodes for gravimetric biosensing. Sensors and Actuators B: Chemical, 2011, 160, 1386-1393.	7.8	42
68	First-Order Elastic Nonlinearities of Bulk Acoustic Wave Resonators. IEEE Transactions on Microwave Theory and Techniques, 2011, 59, 1206-1213.	4.6	13
69	Ar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow /><mml:mrow><mml:mn>3</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math>surface electron gases generated by Ar<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msup><mml:mrow /><mml:mrow><mml:mo>+</mml:mo></mml:mro	3.2	40
70	Growth of AlN oriented films on insulating substrates. , 2011, , .		4
71	Resonant piezoelectric AlN-actuated microcantilevers for detection of antigen/antibody interactions. Proceedings of SPIE, 2011, , .	0.8	1
72	Ta<inf>2</inf>O<inf>5</inf>/SiO<inf>2</inf> insulating acoustic mirrors for AlN-based X-band BAW resonators. , 2011, , .		6

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73	Solidly mounted resonators with carbon nanotube electrodes for biosensing applications. , 2011, , .		0
74	Allâ€Manganite Tunnel Junctions with Interfaceâ€Induced Barrier Magnetism. Advanced Materials, 2010, 22, 5029-5034.	21.0	34
75	Porous silicon oxide sacrificial layers deposited by pulsed-direct current magnetron sputtering for microelectromechanical systems. Thin Solid Films, 2010, 518, 5128-5133.	1.8	10
76	Assessment of solidly mounted resonators with wide-band asymmetric acoustic reflectors. , 2010, , .		4
77	Optimization of thin AlN sputtered films for X-band BAW resonators. , 2010, , .		8
78	Sputtered SiO₂ as low acoustic impedance material for Bragg mirror fabrication in BAW resonators. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2010, 57, 23-29.	3.0	38
79	DCS Tx filters using AlN resonators with iridium electrodes. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2010, 57, 518-523.	3.0	16
80	Response to Comment on â€œColossal Ionic Conductivity at Interfaces of Epitaxial ZrO ₂ :Y ₂ O ₃ /SrTiO ₃ Heterostructuresâ€• Science, 2009, 324, 465-465.	12.6	47
81	Unified model for Bulk Acoustic Wave resonators' nonlinear effects. , 2009, , .		15
82	Sputtered SiO<inf>2</inf> as low acoustic impedance material for Bragg mirror fabrication in BAW resonators. , 2009, , .		4
83	Wide bandwidth Bragg mirrors for multi-band filter chips. , 2009, , .		3
84	Influence of AlN quality on the transverse and longitudinal coupling coefficients of acoustic devices. , 2009, , .		0
85	DCS Tx filters using AlN resonators with iridium electrodes. , 2009, , .		0
86	Silicon oxide sacrificial layers deposited by pulsed-DC magnetron sputtering for MEMS applications. Proceedings of SPIE, 2009, , .	0.8	0
87	Tailoring Disorder and Dimensionality: Strategies for Improved Solid Oxide Fuel Cell Electrolytes. ChemPhysChem, 2009, 10, 1003-1011.	2.1	50
88	AlN films sputtered on iridium electrodes for bulk acoustic wave resonators. Thin Solid Films, 2009, 517, 4673-4678.	1.8	27
89	Aluminum nitride for heatspreading in RF ICâ€™s. Solid-State Electronics, 2008, 52, 1359-1363.	1.4	32
90	Colossal Ionic Conductivity at Interfaces of Epitaxial ZrO ₂ :Y ₂ O ₃ /SrTiO ₃ Heterostructures. Science, 2008, 321, 676-680.	12.6	675

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91	Advanced determination of piezoelectric properties of AlN thin films on silicon substrates. , 2008, , .		4
92	Piezoelectric microresonators based on aluminum Nitride for mass sensing applications. , 2008, , .		0
93	Design of Computer Experiments: A powerful tool for the numerical design of BAW filters. , 2008, , .		4
94	BAW resonators based on AlN with Ir electrodes for digital wireless transmissions. , 2008, , .		8
95	Simulation and laser vibrometry characterization of piezoelectric AlN thin films. Journal of Applied Physics, 2008, 104, .	2.5	42
96	Electrical detection of the mechanical resonances in AlN-actuated microbridges for mass sensing applications. Applied Physics Letters, 2008, 92, .	3.3	18
97	P1H-6 Picosecond Ultrasonics as a Helpful Technique for Introducing a New Electrode Material in BAW Technology: The Iridium Case. Proceedings IEEE Ultrasonics Symposium, 2007, , .	0.0	11
98	P1G-2 Assessment of Aluminum Nitride Films Sputtered on Iridium Electrodes. Proceedings IEEE Ultrasonics Symposium, 2007, , .	0.0	2
99	7E-6 Aluminum Nitride Bulk Acoustic Wave Devices with Iridium Bottom Electrodes. Proceedings IEEE Ultrasonics Symposium, 2007, , .	0.0	3
100	Frequency Characterization of AlN Piezoelectric Resonators. Frequency Control Symposium and Exhibition, Proceedings of the IEEE International, 2007, , .	0.0	1
101	Characterization of PVD aluminum nitride for heat spreading in RF IC's. , 2007, , .		5
102	MEMS Actuated Piezoelectrically with AlN Films. , 2007, , .		1
103	Circuital Model for the Analysis of the Piezoelectric Response of AlN Films Using SAW Filters. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2007, 54, 2367-2375.	3.0	18
104	Combined assessment of piezoelectric AlN films using X-ray diffraction, infrared absorption and atomic force microscopy. Diamond and Related Materials, 2007, 16, 1421-1424.	3.9	43
105	The effect of substrate on high-temperature annealing of GaN epilayers: Si versus sapphire. Journal of Applied Physics, 2006, 100, 043508.	2.5	8
106	Effect of rapid thermal annealing on the crystal quality and the piezoelectric response of polycrystalline AlN films. Thin Solid Films, 2006, 515, 1814-1818.	1.8	45
107	Tunable mechanical resonator with aluminium nitride piezoelectric actuation. , 2006, 6186, 185.		8
108	P3O-2 Fast Evaluation of Piezoelectric Aluminum Nitride Films by Infrared Optical Techniques. , 2006, , .		1

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109	Degradation of the piezoelectric response of sputtered c-axis AlN thin films with traces of non-(0002) x-ray diffraction peaks. Applied Physics Letters, 2006, 88, 161915.	3.3	79
110	Dependence of the IR reflectance LO absorption bands on the crystalline texture of AlN films. Applied Physics Letters, 2006, 88, 231901.	3.3	18
111	<title>Simulation, fabrication, and testing of aluminium nitride piezoelectric microbridges</title>. , 2005, , .		2
112	<title>Ge and GeO<formula><inf><roman>x</roman></inf></formula> films as sacrificial layer for MEMS technology based on piezoelectric AlN: etching and planarization processes (Invited) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 617 T		
113	Piezoelectric actuation of microbridges using AlN. Sensors and Actuators A: Physical, 2005, 123-124, 590-595.	4.1	55
114	Influence of Growth Parameters on the Electrical and Optical Properties of Gex Siy Oz Sputtered Thin Films. , 2005, , 80-84.		0
115	Substrate influence on the high-temperature annealing behavior of GaN: Si vs sapphire. Materials Research Society Symposia Proceedings, 2005, 892, 323.	0.1	0
116	Comparative study of c-axis AlN films sputtered on metallic surfaces. Diamond and Related Materials, 2005, 14, 1198-1202.	3.9	29
117	SAW characteristics of AlN films sputtered on silicon substrates. Ultrasonics, 2004, 42, 403-407.	3.9	92
118	Piezoelectric properties and residual stress of sputtered AlN thin films for MEMS applications. Sensors and Actuators A: Physical, 2004, 115, 501-507.	4.1	100
119	Effect of particle bombardment on the orientation and the residual stress of sputtered AlN films for SAW devices. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2004, 51, 352-358.	3.0	37
120	Piezoelectric properties and residual stress of sputtered AlN thin films for MEMS applications. Sensors and Actuators A: Physical, 2004, 115, 501-501.	4.1	4
121	Influence of oxygen and argon on the crystal quality and piezoelectric response of AlN sputtered thin films. Diamond and Related Materials, 2004, 13, 839-842.	3.9	49
122	Effect of particle bombardment on the orientation and the residual stress of sputtered AlN films for SAW devices. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2004, 51, 352-8.	3.0	2
123	Effect of Particle Bombardment on the Orientation and the Residual Stress of Sputtered AlN Films for SAW Devices. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2004, 51, 352-358.	3.0	1
124	High energy ion characterization of sputtered AlN thin films. Diamond and Related Materials, 2003, 12, 1157-1161.	3.9	7
125	Influence of crystal properties on the absorption IR spectra of polycrystalline AlN thin films. Diamond and Related Materials, 2003, 12, 1186-1189.	3.9	54
126	Influence of sputtering mechanisms on the preferred orientation of aluminum nitride thin films. Journal of Applied Physics, 2003, 94, 1495-1500.	2.5	92

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127	IR uncooled bolometers based on amorphous Ge/sub x/Si/sub 1-x/O/sub y/ on silicon micromachined structures. Journal of Microelectromechanical Systems, 2002, 11, 322-329.	2.5	53
128	Amorphous Ge[sub x]Si[sub 1â^'x]O[sub y] sputtered thin films for integrated sensor applications. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 294.	1.6	13
129	Ge:Si:O evaporated alloys as a thermosensitive layer for large area bolometers. Thin Solid Films, 1999, 337, 253-256.	1.8	7
130	Reactive co-evaporation of Si and Ge in oxygen atmospheres. Thin Solid Films, 1999, 343-344, 13-16.	1.8	0
131	Influence of the deposition parameters on the bonding and optical properties of SiNx ECR films. Journal of Non-Crystalline Solids, 1995, 187, 329-333.	3.1	11
132	Effects of weak intergrain coupling in the transport properties of textured YBCO thin films. Physica C: Superconductivity and Its Applications, 1994, 225, 253-261.	1.2	1
133	Texture improvement of sputtered YBa2Cu3O7â^'x films on MgO (100) with a SrTiO3 buffer layer. Physica C: Superconductivity and Its Applications, 1993, 218, 59-62.	1.2	9
134	Granularity effects in transport properties of 123 superconducting thin films. Journal of Alloys and Compounds, 1993, 195, 635-638.	5.5	3
135	A new design of a semiconductor bolometer on rigid substrate for fusion plasma diagnostics. Review of Scientific Instruments, 1993, 64, 1714-1717.	1.3	6
136	High sensitivity bolometers development. Review of Scientific Instruments, 1992, 63, 4708-4710.	1.3	7
137	Electrical characterization of all-sputtered CdS/CuInSe2 solar cell heterojunctions. Solar Cells, 1990, 28, 31-39.	0.6	6
138	Effect of deposition temperature on the electrical properties of p-type Hg0.8Cd0.2Teî—¸ZnS interface. Journal of Crystal Growth, 1990, 101, 584-588.	1.5	4
139	Photoâ€induced electrical defects in lowâ€temperature photochemical vaporâ€deposited silicon nitride films. Journal of Applied Physics, 1990, 67, 1617-1620.	2.5	2
140	Substrate temperature effect on the optical properties of radioâ€frequency sputtered CuInSe2 thin films. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1989, 7, 1424-1427.	2.1	3
141	Synthesis, characterization and ionic conductivity of Tl(NbTe)O6. Solid State Ionics, 1989, 37, 87-93.	2.7	5
142	Role of deep levels and interface states in the capacitance characteristics of allâ€sputtered CuInSe2/CdS solar cell heterojunctions. Journal of Applied Physics, 1989, 65, 3236-3241.	2.5	13
143	Effects of argon partial pressure and hydrogen admixtures on the properties of sputtered CuInSe2 thin films. Applied Surface Science, 1988, 33-34, 844-853.	6.1	1
144	Influence of interface states on the electrical characteristics of all-sputtered solar cells. Solar Energy Materials and Solar Cells, 1988, 17, 279-287.	0.4	4

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145	Synthesis and ionic conductivity of mixed oxides (H2ONH4)MTeO6.5 (M = Cr, W). Materials Research Bulletin, 1988, 23, 1107-1117.	5.2	1
146	Capacitance characterisation of Cu2S/CdS heterojunctions. Semiconductor Science and Technology, 1988, 3, 781-785.	2.0	14
147	CuInSe2thin films produced by rf sputtering in Ar/H2atmospheres. Journal of Applied Physics, 1987, 62, 4163-4169.	2.5	35
148	Sputtering process of Cu2S in an Ar atmosphere. Vacuum, 1987, 37, 433-436.	3.5	4
149	Thin CuxS sputtered films in Ar/H2 atmospheres. Vacuum, 1987, 37, 437-439.	3.5	9
150	Effects of residual gases and rf power on ITO rf sputtered thin films. Vacuum, 1987, 37, 447-449.	3.5	9
151	Sputtering of SiO2 in O2î—Ar atmospheres. Thin Solid Films, 1986, 139, 201-208.	1.8	13
152	Electrical properties of R.F.-sputtered SiO2 films. Thin Solid Films, 1985, 125, 299-303.	1.8	6
153	Role of argon ion bombardment in sputtered AlN films for SAW devices. , 0, , .		1
154	SAW and BAW response of c-axis AlN thin films sputtered on platinum. , 0, , .		3
155	A model for the accurate determination of the electromechanical coupling factor of thin film SAW devices on non-insulating substrates. , 0, , .		9
156	Assessment of the piezoelectric response of sputtered A1N films by x-ray diffraction. , 0, , .		1
157	AlN-on-Si SAW filters: influence of film thickness, IDT geometry and substrate conductivity. , 0, , .		2